Pradipta Dutta

List of Publications by Year
in descending order

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15 papers	57 citations	1937685 4 h-index	1872680 6 g-index

15 all docs	15 docs citations	15 times ranked	40 citing authors

#	Article	IF	Citations
1	Muti-Carrier CDMA overview with BPSK modulation in Rayleigh channel. , 2010, , .		12
2	Impact of high mobility IIIâ€Ⅴ compound material of a short channel thinâ€film SiGe double gate junctionless MOSFET as a source. Engineering Reports, 2020, 2, e12086.	1.7	11
3	A 2-D surface-potential-based threshold voltage model for short channel asymmetric heavily doped DG MOSFETs. International Journal of Numerical Modelling: Electronic Networks, Devices and Fields, 2014, 27, 682-690.	1.9	6
4	An Analytical BTBT Current Model of Symmetric/Asymmetric 4T Tunnel Double Gate FETs With Ambipolar Characteristic. IEEE Transactions on Electron Devices, 2016, 63, 2700-2707.	3.0	6
5	Comparison Study of DG-MOSFET with and without Gate Stack Configuration for Biosensor Applications. Silicon, 2022, 14, 3629-3640.	3.3	6
6	Improvement of transconductance and cut-off frequency in $$hbox {In}_{0.1}hbox {Ga}_{0.9}hbox {N}$$ back-barrier-based double-channel Al$$_{0.3}$$Ga$$_{0.7}$$NÃ/ÂGaN high electron mobility transistor by enhancing the drain source contact length ratio. Pramana - Journal of Physics, 2020, 94, 1.	1.8	4
7	Performance analysis of junctionless double gate MOSFET using Silicon and In<inf>0.53</inf>Ga<inf>0.47</inf>As. , 2016, , .		3
8	Short-channel drain current model for asymmetric heavilyÂ/Âlightly doped DG MOSFETs. Pramana - Journal of Physics, 2017, 89, 1.	1.8	3
9	A dual gate material tunnel field effect transistor model incorporating twoâ€dimensional Poisson and Schrodinger wave equations. International Journal of Numerical Modelling: Electronic Networks, Devices and Fields, 0, , e2933.	1.9	2
10	Improvement of transconductance and gate source capacitance of Al<inf>0.27</inf>Ga<inf>0.73</inf>N/GaN HEMT at 45nm gate length with In<inf>0.1</inf>Ga<inf>0.9</inf>N back-barrier. , 2017, , .		1
11	Controlling of Floating-Body and Thermal Conductivity in Short Channel SOI MOSFET at 30Ânm Channel Node. Silicon, 0, , 1.	3.3	1
12	Improvements in FOMs and Thermal Effects of a III-V Compound Material Based Short-Channel Thin Film Junctionless Double Gate MOSFETs. ECS Journal of Solid State Science and Technology, 2021, 10, 111006.	1.8	1
13	Improvement in the Performance of III-V Channel Based Ultra-Thin Junction-Less-Hybrid CMOS Circuits with Mixed Mode Analysis. ECS Journal of Solid State Science and Technology, 2022, 11, 051001.	1.8	1
14	Performance enhancement in Al<inf>0.3</inf>Ga<inf>0.7</inf>N/GaN HEMT based inverter using MOSHEMT. , 2017, , .		0
15	Impact of Left Side Back Gate Misalignment Effect in an Analytical Tunneling Current Modeling of an Ultrathin Asymmetric DG TFET. Silicon, 2021, 13, 929-938.	3.3	0